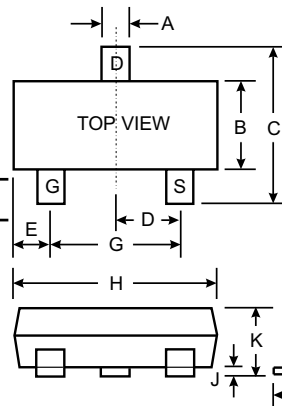


**Features**

- High Breakdown Voltage
- High Input Impedance
- Fast Switching Speed
- Specially Suited for Telephone Subsets
- Ideal for Automated Surface Mount Assembly

**Mechanical Data**

- Case: SOT-23, Plastic
- Terminals: Solderable per MIL-STD-202 Method 208
- Pin Connection: See Diagram
- Marking: S07
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178
All Dimensions in mm		

**Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	200	V
Drain-Gate Voltage	V <sub>DGS</sub>	200	V
Gate-Source Voltage (pulsed) (Note 2)	V <sub>GS</sub>	±20	V
Drain Current (continuous)	I <sub>D</sub>	100	mA
Power Dissipation @ T <sub>C</sub> = 50°C (Note 1)	P <sub>d</sub>	310	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Inverse Diode** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Max Forward Current (continuous)	I <sub>F</sub>	0.3	A
Forward Voltage Drop (typ) @ V <sub>GS</sub> = 0, I <sub>F</sub> = 0.3A, T <sub>J</sub> = 25°C	V <sub>F</sub>	0.85	V

- Notes: 1. Device mounted on ceramic substrate 0.7mm x 2.5cm<sup>2</sup> area.  
2. Pulse test: Pulse width = 80µs, duty cycle = 1%.

**Electrical Characteristics** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	200	230	—	V	$I_D = 100\mu\text{A}, V_{GS} = 0$
Gate-Body Leakage Current	$I_{GSS}$	—	—	10	nA	$V_{GS} = 15\text{V}, V_{DS} = 0$
Drain-Source Cutoff Current	$I_{DSS}$ $I_{DSX}$	—	—	30 1.0	nA $\mu\text{A}$	$V_{DS} = 130\text{V}, V_{GS} = 0$ $V_{DS} = 70\text{V}, V_{GS} = 0.2\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	—	1.8	3.0	V	$V_{GS} = V_{DS}, I_D = 1.0\text{mA}$
Drain-Source ON Resistance	$r_{DS(ON)}$	—	18	28	$\Omega$	$V_{GS} = 2.8\text{V}, I_D = 20\text{mA}$
Thermal Resistance, Junction to Substrate Backside	$R_{\theta JSB}$	—	—	320	K/W	Note 1
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	—	—	400	K/W	Note 1
Input Capacitance Output Capacitance Feedback Capacitance	$C_{iss}$ $C_{oss}$ $C_{rss}$	—	58 8.0 1.5	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0, f = 1.0\text{MHz}$

- Notes: 1. Device mounted on ceramic substrate 0.7mm x 2.5cm<sup>2</sup> area.  
2. Pulse test: Pulse width = 80 $\mu\text{s}$ , duty cycle = 1%.

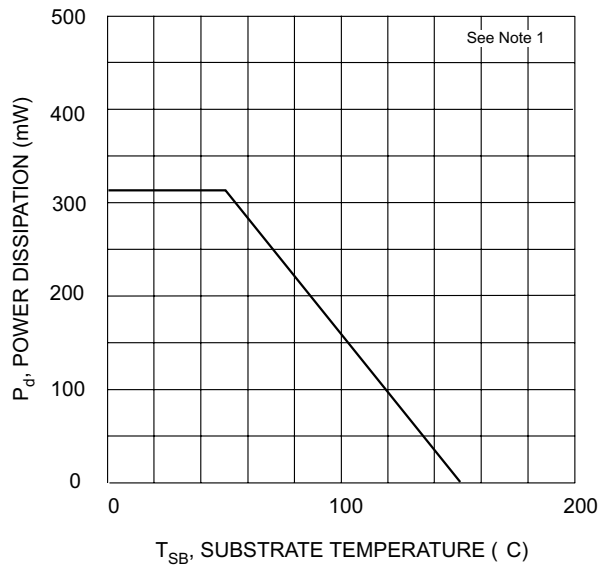


Fig. 1, Power Derating Curve

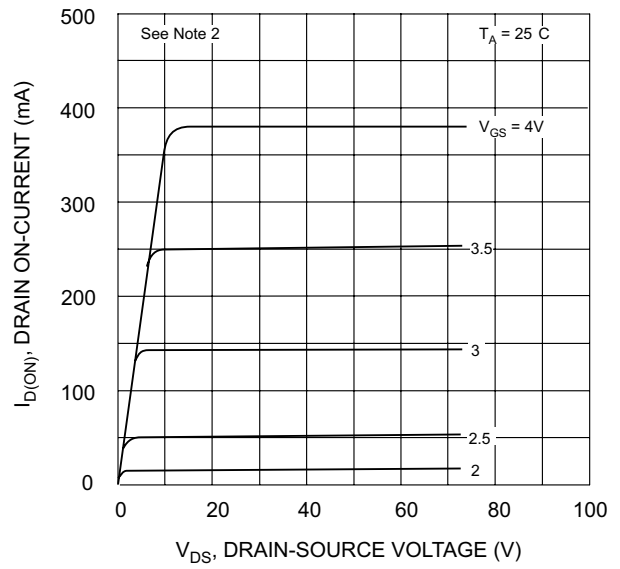


Fig. 2, Output Characteristics

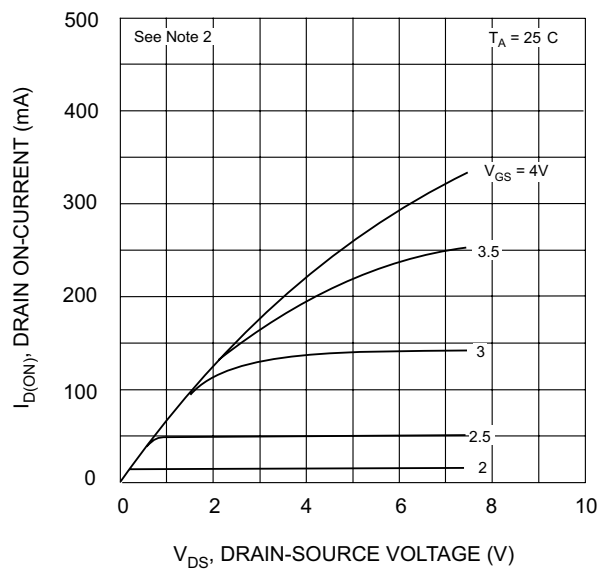


Fig. 3, Saturation Characteristics

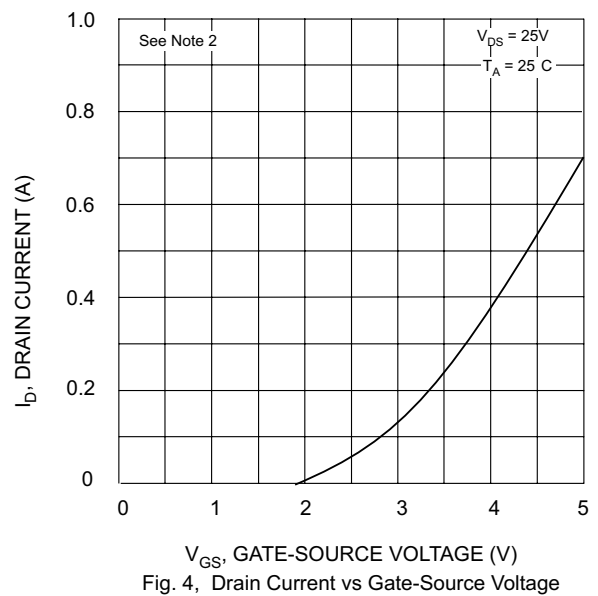


Fig. 4, Drain Current vs Gate-Source Voltage

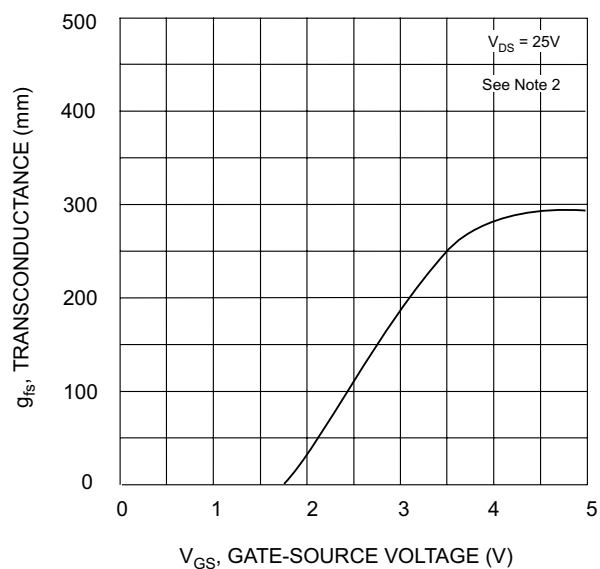


Fig. 5, Transconductance vs Gate-Source Voltage

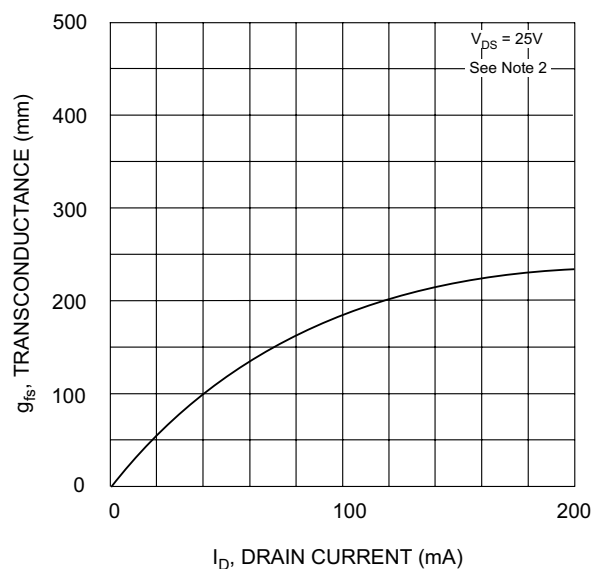


Fig. 6, Transconductance vs Drain Current